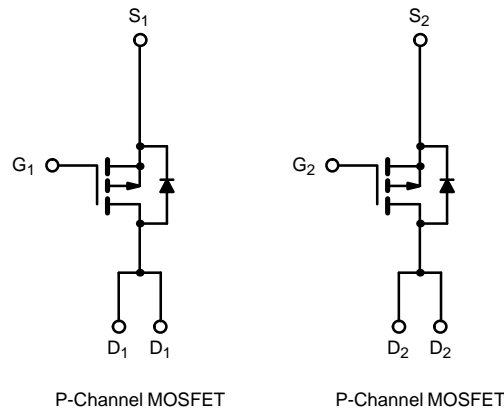
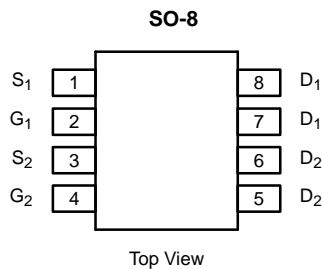




## Dual P-Channel 2.5-V (G-S) MOSFET

**2.5-V Rated**

PRODUCT SUMMARY		
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)
-12	0.05 @ V <sub>GS</sub> = -4.5 V	± 5
	0.074 @ V <sub>GS</sub> = -2.5 V	± 4.1



ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V <sub>DS</sub>	-12	V
Gate-Source Voltage		V <sub>GS</sub>	± 8	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	I <sub>D</sub>	± 5	A
	T <sub>A</sub> = 70 °C		± 4.0	
Pulsed Drain Current		I <sub>DM</sub>	± 20	
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	-1.7	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C	P <sub>D</sub>	2.0	W
	T <sub>A</sub> = 70 °C		1.3	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Maximum Junction-to-Ambient <sup>a</sup>	R <sub>thJA</sub>	62.5	°C/W

Notes

a. Surface Mounted on FR4 Board, t ≤ 10 sec.

For SPICE model information via the Worldwide Web: <http://www.vishay.com/www/product/spice.htm>



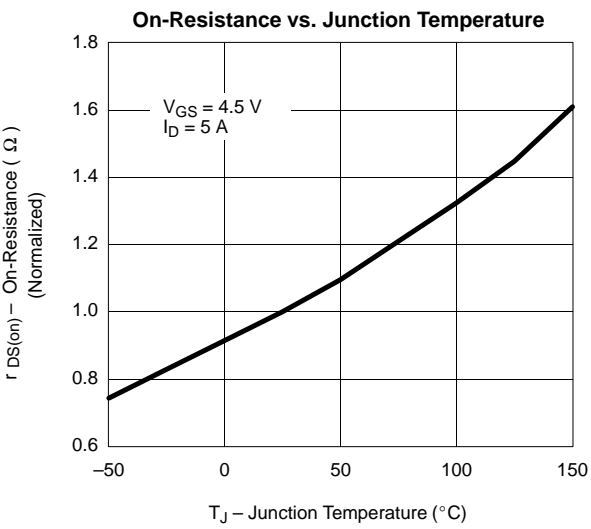
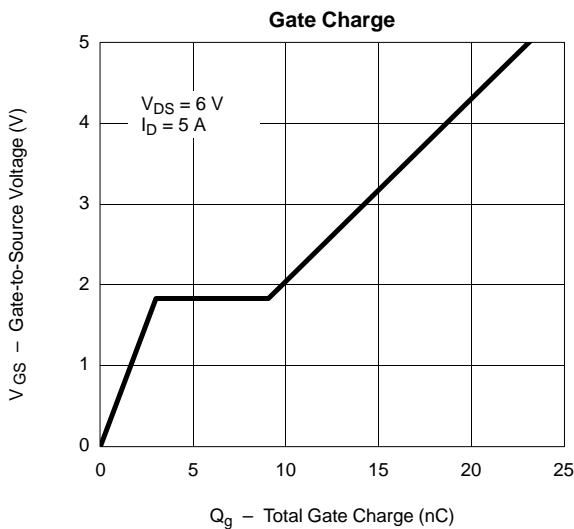
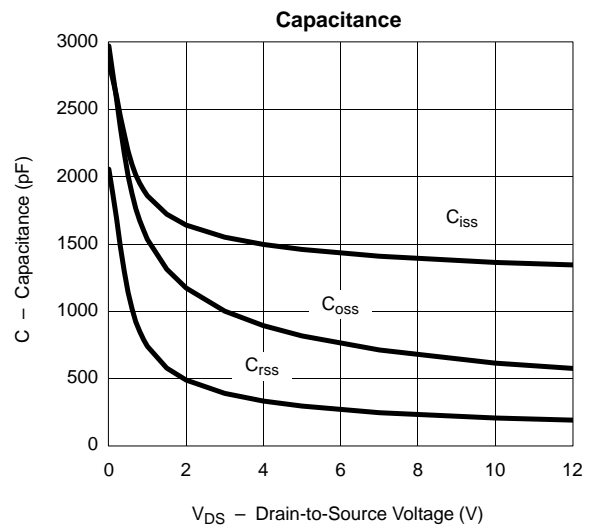
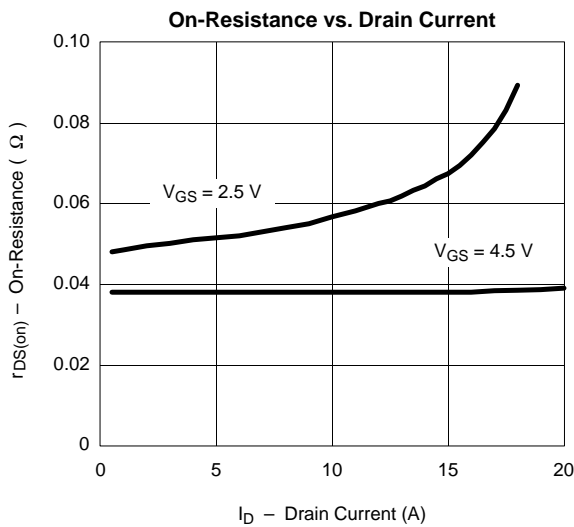
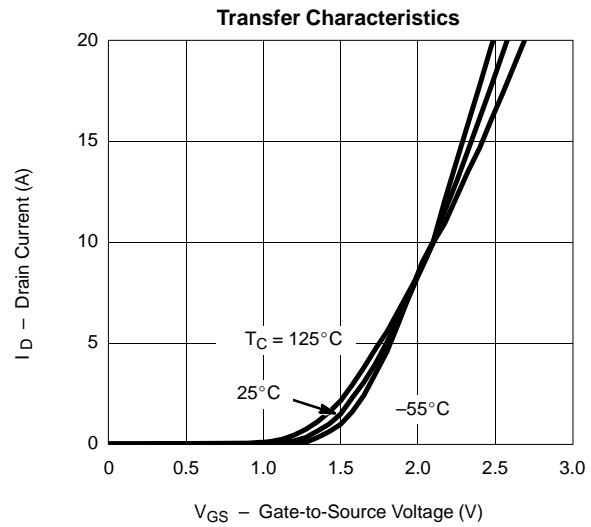
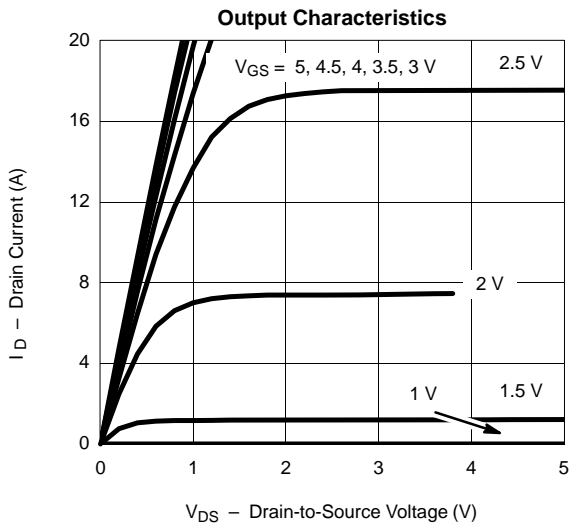
<b>SPECIFICATIONS (T<sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)</b>						
Parameter	Symbol	Test Condition	Min	Typ <sup>a</sup>	Max	Unit
<b>Static—0.6</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-0.6			V
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±8 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -12 V, V <sub>GS</sub> = 0 V			-1	μA
		V <sub>DS</sub> = -12 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55°C			-5	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = -4.5 V	-20			A
		V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = -2.5 V	-6			
Drain-Source On-State Resistance <sup>b</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -5 A		0.039	0.05	Ω
		V <sub>GS</sub> = -2.5 V, I <sub>D</sub> = -3 A		0.051	0.074	
Forward Transconductance <sup>b</sup>	g <sub>fs</sub>	V <sub>DS</sub> = -9 V, I <sub>D</sub> = -5 A		16		S
Diode Forward Voltage <sup>b</sup>	V <sub>SD</sub>	I <sub>S</sub> = -1.7 A, V <sub>GS</sub> = 0 V		-0.75	-1.2	V
<b>Dynamic<sup>a</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -6 V, V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -5 A		21	40	nC
Gate-Source Charge	Q <sub>gs</sub>			3		
Gate-Drain Charge	Q <sub>gd</sub>			6		
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = -6 V, R <sub>L</sub> = 6 Ω I <sub>D</sub> ≅ -1 A, V <sub>GEN</sub> = -4.5 V, R <sub>G</sub> = 6 Ω		20	40	ns
Rise Time	t <sub>r</sub>			40	80	
Turn-Off Delay Time	t <sub>d(off)</sub>			100	200	
Fall Time	t <sub>f</sub>			60	120	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = -1.7 A, di/dt = 100 A/μs		67	100	

Notes

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.



**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**



**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**

